

## 600V, 7A, Trench FS II Fast IGBT

### General Description

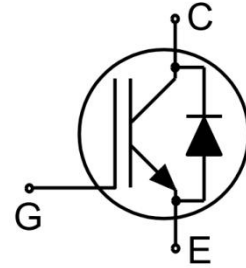
Using NCE's proprietary trench design and advanced FS (Field Stop) second generation technology, the 600V Trench FSII IGBT offers superior conduction and switching performances, and easy parallel operation;

### Features

- Trench FSII Technology Offering
- Very low  $V_{CE(sat)}$
- High speed switching
- Positive temperature coefficient in  $V_{CE(sat)}$
- Very tight parameter distribution
- High ruggedness, temperature stable behavior

### Application

- Air Condition
- Inverters
- Motor drives



Schematic diagram

### Package Marking and Ordering Information

Device	Device Package	Device Marking
NCE07TD60BI	TO-251	NCE07TD60BI



TO-251

### Absolute Maximum Ratings ( $T_C=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
$V_{CES}$	Collector-Emitter Voltage	600	V
$V_{GES}$	Gate- Emitter Voltage	$\pm 30$	V
$I_C$	Collector Current	14	A
	Collector Current @ $T_C = 100^{\circ}\text{C}$	7	A
$I_{Cpuls}$	Pulsed Collector Current, $t_p$ limited by $T_{jmax}$	21	A
-	turn off safe operating area, $V_{CE}=600\text{V}$ , $T_J=175^{\circ}\text{C}$	21	A
$I_F$	Diode Continuous Forward Current @ $T_C = 100^{\circ}\text{C}$	7	A
$I_{FM}$	Diode Maximum Forward Current	21	A
$P_D$	Power Dissipation @ $T_C = 25^{\circ}\text{C}$	87	W
	Power Dissipation @ $T_C = 100^{\circ}\text{C}$	43.5	W
$T_J, T_{stg}$	Operating Junction and Storage Temperature Range	-55 to +175	$^{\circ}\text{C}$
$T_L$	Maximum Temperature for Soldering	260	$^{\circ}\text{C}$
$t_{sc}$	Short circuit withstand time $V_{GE}=15\text{V}$ , $V_{CC}\leq 400\text{V}$ , Allowed number of short circuits<1000Time between short circuits: $\geq 1.0\text{s}$ , $T_J\leq 150^{\circ}\text{C}$	5	us

**Thermal Characteristic**

Symbol	Parameter	Value	Units
$R_{\theta JC}$	Thermal Resistance, Junction to case for IGBT	1.71	$^{\circ}\text{C}/\text{W}$
$R_{\theta JC}$	Thermal Resistance, Junction to case for Diode	2.50	$^{\circ}\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	62	$^{\circ}\text{C}/\text{W}$

**Electrical Characteristics ( $T_c=25^{\circ}\text{C}$  unless otherwise noted)**

Symbol	Parameter	Conditions	Value			Units
			Min.	Typ.	Max.	
<b>Static Characteristics</b>						
$V_{(BR)CES}$	Collector-Emitter Breakdown Voltage	$V_{GE}=0\text{V}, I_{CE}=1\text{mA}$	600	--	--	V
$I_{CES}$	Collector-Emitter Leakage Current	$V_{GE}=0\text{V}, V_{CE}=600\text{V}$	--	--	4	$\mu\text{A}$
$I_{GES(F)}$	Gate to Emitter Forward Leakage	$V_{GE}=+30\text{V}, V_{CE}=0\text{V}$	--	--	200	nA
$I_{GES(R)}$	Gate to Emitter Reverse Leakage	$V_{GE}=-30\text{V}, V_{CE}=0\text{V}$	--	--	200	nA
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=5\text{A}$ $V_{GE}=15\text{V}$	--	1.7	1.9	V
		$T_J=25^{\circ}\text{C}$ $T_J=175^{\circ}\text{C}$	--	1.9	--	V
$V_{GE(th)}$	Gate Threshold Voltage	$I_C=1\text{mA}, V_{CE}=V_{GE}$	4.0	5.0	6.0	V
<b>Dynamic Characteristics</b>						
$C_{ies}$	Input Capacitance	$V_{CE}=25\text{V}, V_{GE}=0\text{V},$ $f=1\text{MHz}$	--	675	--	pF
$C_{oes}$	Output Capacitance		--	22	--	
$C_{res}$	Reverse Transfer Capacitance		--	13	--	
$Q_g$	Total Gate Charge	$V_{CC}=480\text{V}, I_C=7\text{A},$ $V_{GE}=15\text{V}$	--	28	--	nC
$Q_{ge}$	Gate to Emitter Charge		--	8	--	
$Q_{gc}$	Gate to Collector Charge		--	13	--	
$I_{C(SC)}$	Short circuit collector current Max.1000 short circuits Time between short circuits: $\geq 1.0\text{s}$	$V_{GE}=15\text{V}, V_{CC}\leq 400\text{V},$ $t_{sc}\leq 5\mu\text{s}, T_J\leq 150^{\circ}\text{C}$	--	34	--	A
<b>Switching Characteristics</b>						
$t_{d(ON)}$	Turn-on Delay Time	$V_{CC}=400\text{V}, I_C=7\text{A},$ $V_{GE}=0/15\text{V}, R_g=5\Omega$ Inductive Load	--	20	--	ns
$t_r$	Rise Time		--	15	--	
$t_{d(OFF)}$	Turn-Off Delay Time		--	73	--	
$t_f$	Fall Time		--	18	--	
$E_{on}$	Turn-On Switching Loss		--	0.21	--	mJ
$E_{off}$	Turn-Off Switching Loss		--	0.10	--	
$E_{ts}$	Total Switching Loss		--	0.31	--	

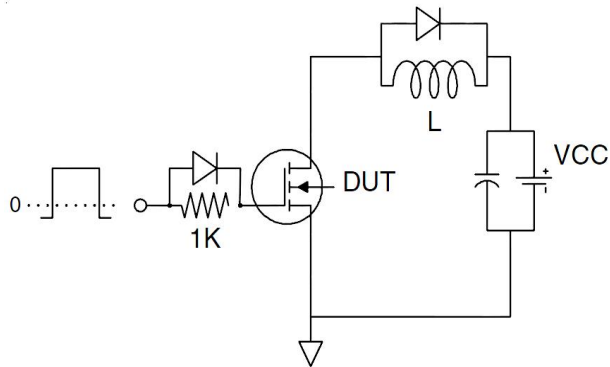
**Electrical Characteristics of the Diode ( $T_c=25^{\circ}\text{C}$  unless otherwise specified)**

Symbol	Parameter	Conditions	Rating			Units
			Min.	Typ.	Max.	
$V_{FM}$	Diode Forward Voltage	$I_F=7\text{A}$	--	1.75	2.40	V
$T_{rr}$	Reverse Recovery Time	$I_F=7\text{A},$ $di/dt=200\text{A}/\mu\text{s}$	--	230	--	ns
$I_{RRM}$	Diode Peak Reverse Recovery Current		--	3.5	--	A
$Q_{rr}$	Reverse Recovery Charge		--	0.44	--	$\mu\text{C}$

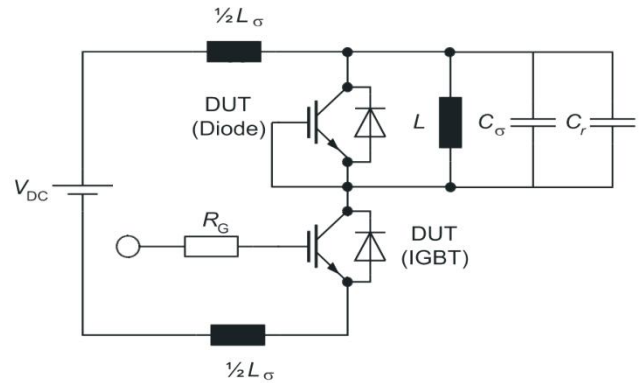
Pulse width  $t_p\leq 380\mu\text{s}, \delta\leq 2\%$

## Test Circuit

### 1) Gate Charge Test Circuit

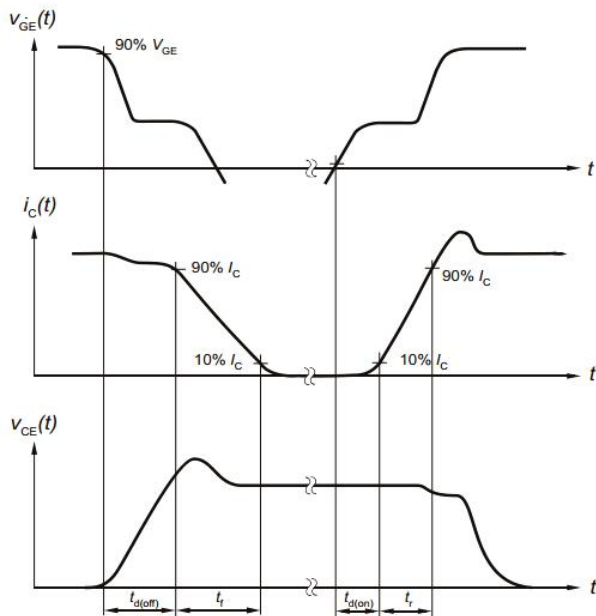


### 2) Switch Time Test Circuit

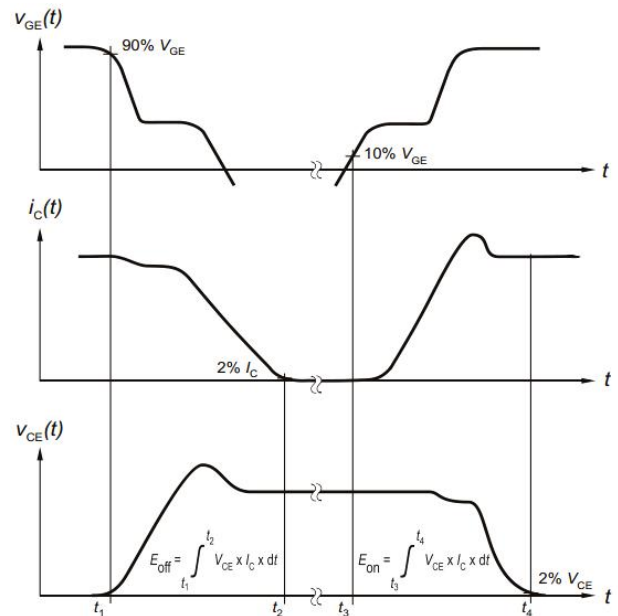


## Switching characteristics

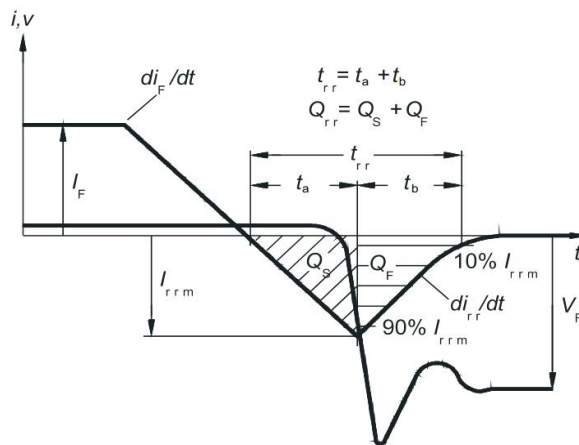
### 1) Definition of switching times



### 2) Definition of switching losses



### 3) Definition of diode switching characteristics



Typical Electrical and Thermal Characteristics

Figure 1 Output Characteristics

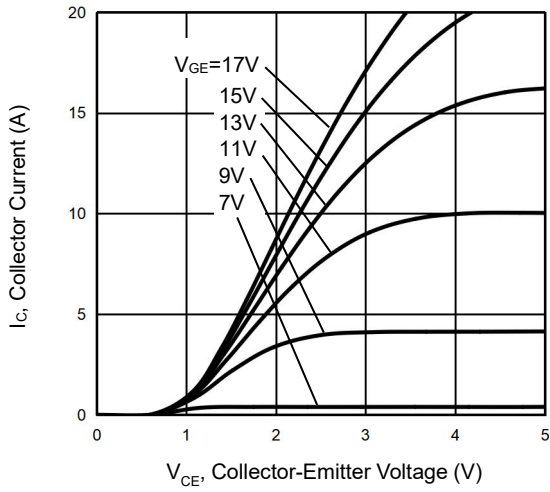


Figure 2 Transfer Characteristics

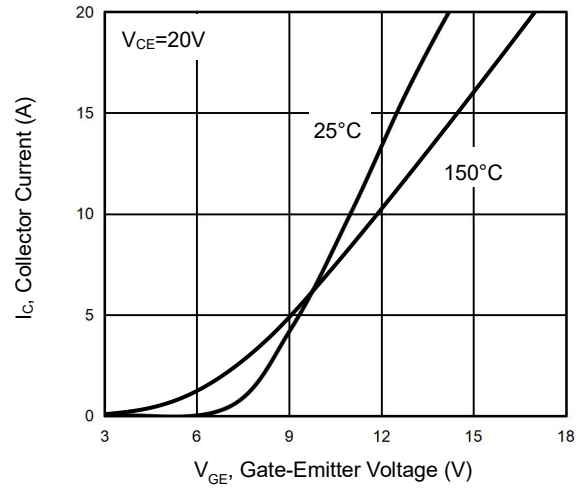


Figure 3  $V_{CEsat}$  vs. Case Temperature

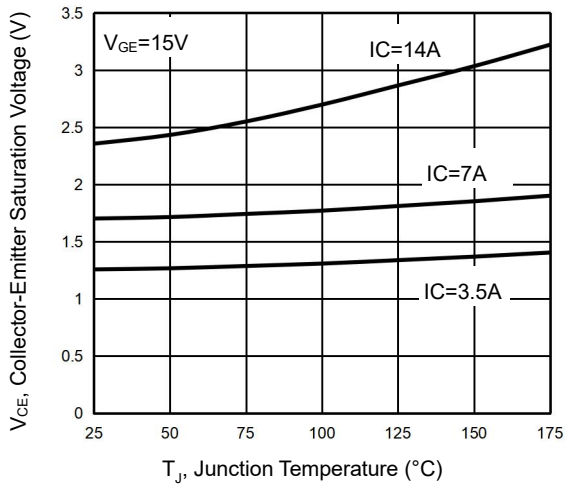


Figure 4 Saturation Voltage vs.  $V_{GE}$

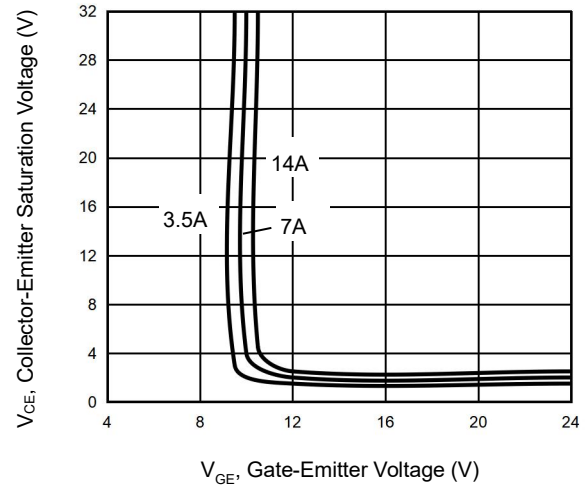


Figure 5 Capacitance Characteristics

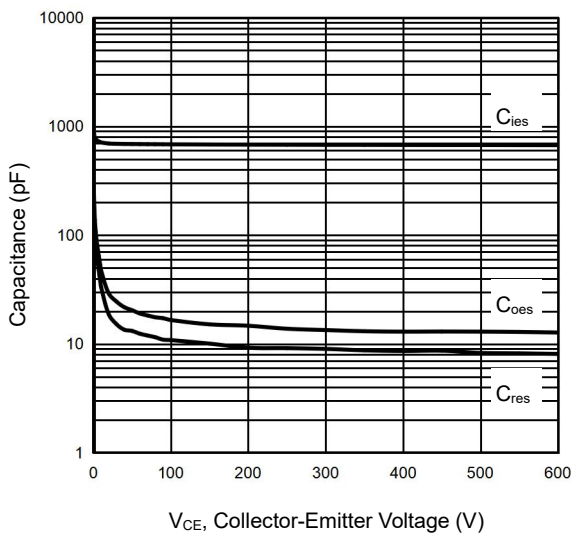
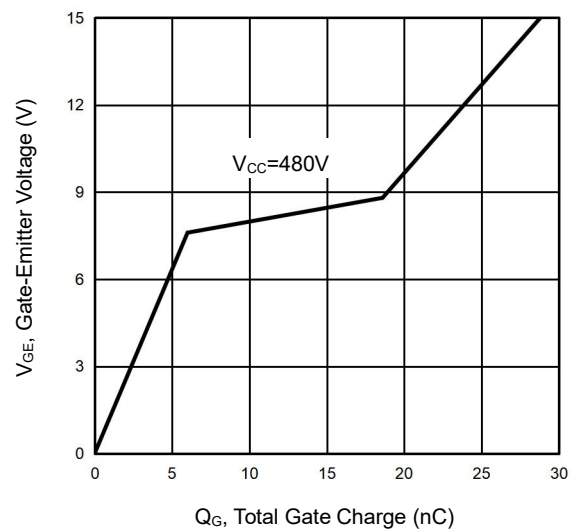


Figure 6 Gate charge waveform



Typical Electrical and Thermal Characteristics

Figure 7 Forward Characteristics

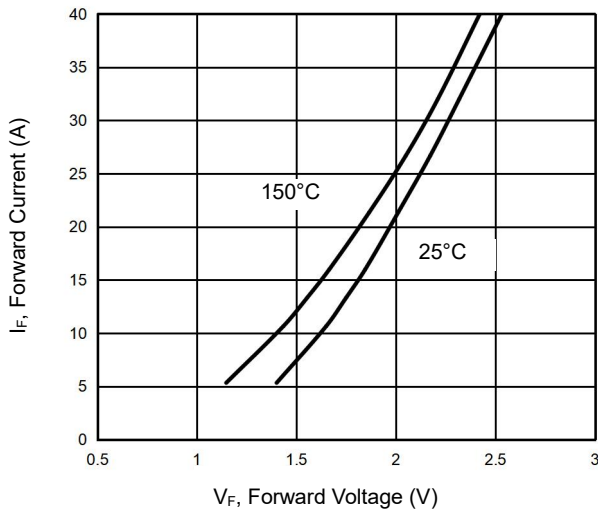


Figure 8  $V_F$  vs. Temperature

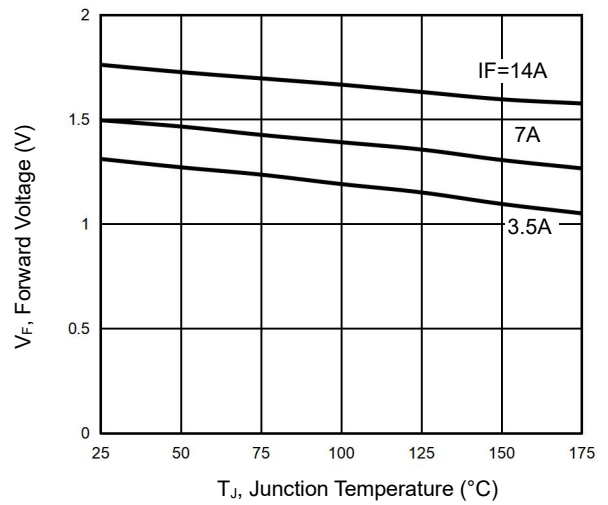


Figure 9 Typical Switching Times as a Function of Gate Resistor

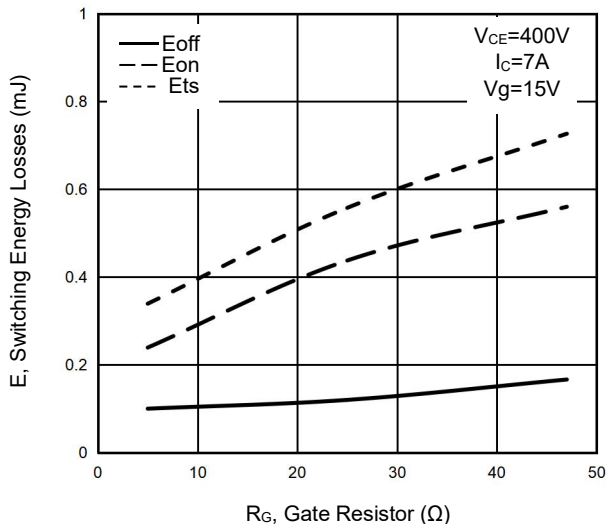


Figure 10 Typical Switching Times as a Function of Junction Temperature

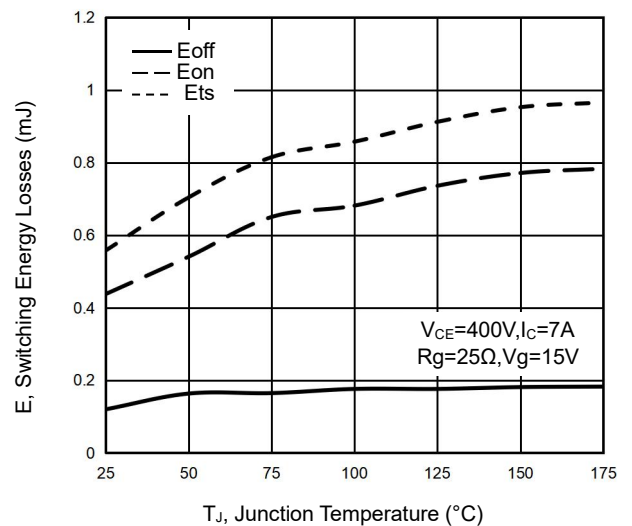


Figure 11 Gate-emitter Threshold Voltage as a Function of Junction Temperature

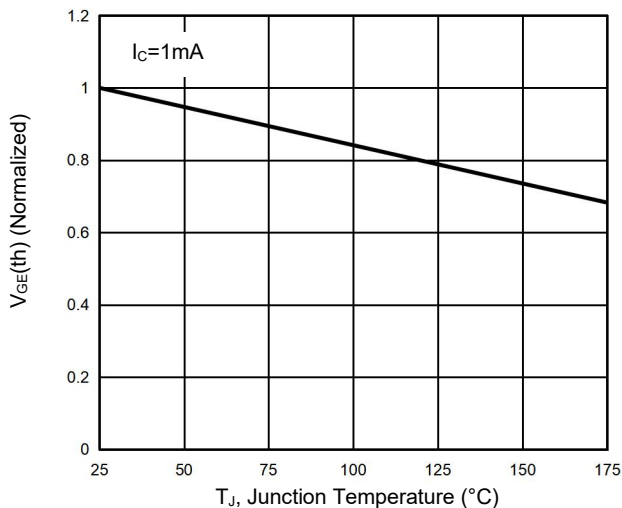
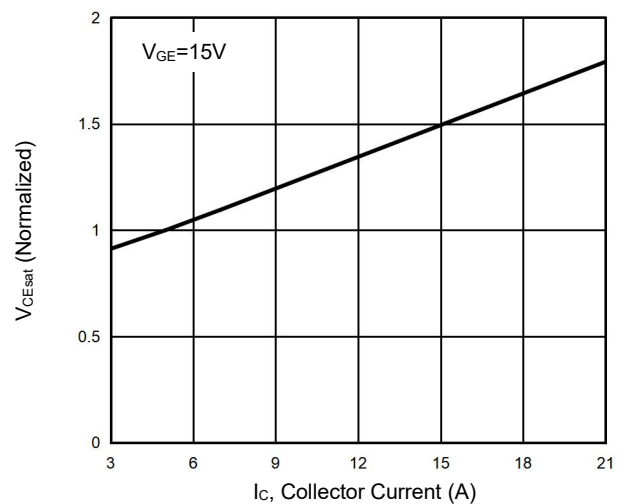
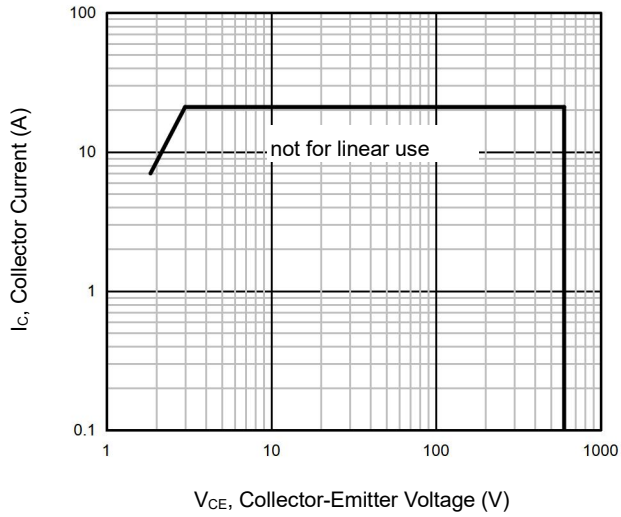


Figure 12 Typical Collector-emitter Saturation Voltage as a function of Collector Current

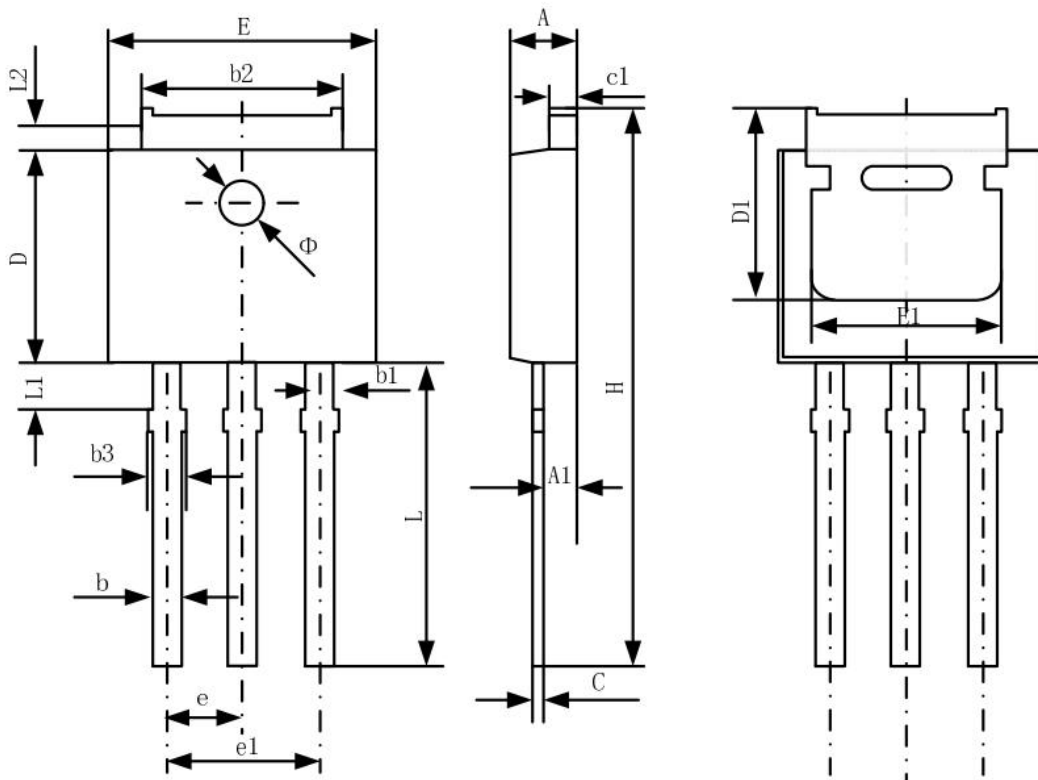


### Typical Electrical and Thermal Characteristics

Figure 13 Forward Bias Safe Operating Area



## TO-251 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.20	2.35	0.087	0.093
A1	0.90	1.10	0.035	0.043
b	0.56	0.69	0.022	0.027
b1	0.77	0.90	0.030	0.035
b2	5.23	5.43	0.206	0.214
b3		1.05		0.041
C	0.46	0.59	0.018	0.023
c1	0.46	0.59	0.018	0.023
D	6.00	6.20	0.236	0.244
D1	5.20		0.205	
E	6.50	6.70	0.256	0.264
E1	4.60	5.00	0.181	0.197
e	2.24	2.34	0.088	0.092
e1	4.47	4.67	0.176	0.184
H	16.18	16.78	0.637	0.661
L	9.00	9.60	0.354	0.378
L1	0.95	1.35	0.037	0.053
L2	0.90	1.25	0.035	0.049

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